

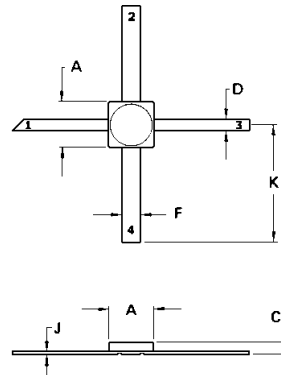
# SILICON NPN RF TRANSISTOR

**DESCRIPTION:**

The **MRF572** is Designed for Low Noise General Purpose VHF,UHF Amplifier and Oscillator Applications.

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	60 mA
<b>V<sub>CE</sub></b>	12 V
<b>P<sub>DISS</sub></b>	500 mW @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C

**PACKAGE STYLE 100MIL CERAMIC STRIPLINE**


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.29	2.67	0.090	0.105
C	0.89	1.40	0.035	0.055
D	0.41	0.61	0.016	0.024
F	0.89	1.09	0.035	0.043
J	0.08	0.15	0.003	0.006
K	4.45	5.84	0.175	0.230

1 = Collector    2 & 4 = Emitter  
3 = Base

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 1.0 mA		12			V
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 100 μA		20			V
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 8.0 V				200	μA
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 50 μA		1.5			V
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 8.0 V	I <sub>C</sub> = 10 mA	30		300	---
<b>C<sub>cb</sub></b>	V <sub>CB</sub> = 8.0 V			0.25		pF
<b>f<sub>t</sub></b>	V <sub>CE</sub> = 8.0 V	I <sub>C</sub> = 25 mA		8.0		GHz
<b> S<sub>21E</sub> <sup>2</sup></b>	V <sub>CE</sub> = 8.0 V    I <sub>C</sub> = 25 mA			16.9		dB
			f = 2.0 GHz	12.0		
<b>GNF</b>	V <sub>CE</sub> = 8.0 V    I <sub>C</sub> = 0 mA			16.5		dB
			f = 1.0 GHz	12		
			f = 2.0 GHz	10		
<b>NF</b>	V <sub>CE</sub> = 8.0 V    I <sub>C</sub> = 0 mA			1.0	2.0	dB
			f = 1.0 GHz	1.5		
			f = 2.0 GHz	2.5		